US009411232B2

(12) **United States Patent**
Nagahara et al.

(10) **Patent No.: US 9,411,232 B2**
(45) **Date of Patent: Aug. 9, 2016**

(54) **COMPOSITION FOR FORMING FINE RESIST PATTERN, AND PATTERN FORMATION METHOD USING SAME**

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(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

(21) Appl. No.: **14/770,694**

(22) PCT Filed: **Mar. 14, 2014**

(86) PCT No.: **PCT/JP2014/056983**

§ 371 (c)(1),
(2) Date: **Aug. 26, 2015**

(87) PCT Pub. No.: **WO2014/136991**

PCT Pub. Date: **Sep. 12, 2014**

(65) **Prior Publication Data**

US 2016/0011508 A1 Jan. 14, 2016

(30) **Foreign Application Priority Data**

Mar. 5, 2013 (JP) 2013-043177

(51) **Int. Cl.**

G03F 7/11	(2006.01)
G03F 7/40	(2006.01)
G03F 7/09	(2006.01)
H01L 21/027	(2006.01)
H01L 21/768	(2006.01)
C08L 33/14	(2006.01)
C09D 139/04	(2006.01)
G03F 7/039	(2006.01)
G03F 7/16	(2006.01)
G03F 7/20	(2006.01)
G03F 7/32	(2006.01)

(52) **U.S. Cl.**

CPC . ***G03F 7/11*** (2013.01); ***C08L 33/14*** (2013.01); ***C09D 139/04*** (2013.01); ***G03F 7/039*** (2013.01); ***G03F 7/0392*** (2013.01); ***G03F 7/094*** (2013.01); ***G03F 7/16*** (2013.01); ***G03F 7/168*** (2013.01); ***G03F 7/20*** (2013.01); ***G03F 7/32*** (2013.01); ***G03F 7/40*** (2013.01); ***G03F 7/405*** (2013.01); ***H01L 21/0274*** (2013.01); ***H01L 21/76816*** (2013.01)

(58) **Field of Classification Search**

CPC G03F 7/11; G03F 7/40; G03F 7/094; G03F 7/38; G03F 7/168; H01L 21/0273; H01L 21/0274; H01L 21/0275; H01L 21/312; H01L 21/76816; C08L 33/14; C09D 139/00; C09D 139/02; C09D 139/04

USPC 430/270.1, 271.1, 322, 325, 329, 330, 430/331, 324, 269, 394, 906, 964; 438/725, 438/780, 700, 702, 760; 525/374, 379; 427/97.1, 97.2, 97.6

See application file for complete search history.

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(57) **ABSTRACT**

The present invention provides a composition enabling to form a fine negative photoresist pattern less suffering from surface roughness, and also provides a pattern formation method employing that composition. The composition is used for miniaturizing a resist pattern by fattening in a process of forming a positive resist pattern from a chemically amplified positive-working type resist composition, and it contains a polymer comprising a repeating unit having an amino group, a solvent, and an acid. In the pattern formation method, the composition is cast on a positive photoresist pattern beforehand obtained by development and is then heated to form a fine pattern.

16 Claims, No Drawings